## Amendments to the Claims:

said high-frequency power supply.

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1. (Original) A method of cleaning a substrate processing apparatus comprising a processing container defined by an outer wall, a holding stage connected to a high-frequency power supply and provided in said processing container for holding a processing substrate, an exhaust port for evacuating the inside of said processing container, a microwave transmissive window provided on said processing container as part of said outer wall so as to face said processing substrate, a microwave antenna provided on said microwave transmissive window and electrically connected to a microwave power supply, a plasma gas supply portion for supplying a plasma gas into said processing container, and a process gas supply portion provided between said processing substrate on said holding stage and said microwave transmissive window so as to face said processing substrate, said method comprising:

a gas introducing step of introducing a cleaning gas into said processing container, a plasma exciting step of introducing a microwave into said processing container from said microwave antenna to thereby excite a plasma in said processing container, and a bias applying step of applying a high-frequency power to said holding stage from

- 2. (Original) The method according to claim 1, wherein said process gas supply portion is made of a conductive material and grounded.
- 3. (Currently Amended) The method according to claim 1 [[or 2]], wherein said microwave antenna is power-fed through a coaxial waveguide and comprises an antenna body having an opening portion, a microwave radiating surface having a plurality of slots and provided on said antenna body so as to cover said opening portion, and a dielectric provided between said antenna body and said microwave radiating surface.
- 4. (Currently Amended) The method according to any one of claims 1 to 3 claim 1, wherein said cleaning gas contains oxygen.

- 5. (Currently Amended) The method according to any one of claims 1 to 4 claim

  1, wherein said cleaning gas contains hydrogen.
- 6. (Currently Amended) The method according to any one of claims 1 to 5 claim 1, wherein said cleaning gas contains H<sub>2</sub>O.
- 7. (Currently Amended) The method according to any one of claims 1 to 6 claim 1, wherein said cleaning gas contains a fluorine compound.
- 8. (Currently Amended) The method according to any one of claims 1 to 7 claim 1, wherein said cleaning gas is introduced from said plasma gas supply portion provided between said microwave antenna and said process gas supply portion.
- 9. (Currently Amended) The method according to any one of claims 1 to 8 claim 1, wherein said cleaning gas is introduced from said process gas supply portion.
- 10. (Currently Amended) The method according to any one of claims 1 to 9 claim 1, wherein said cleaning gas is dissociated by said microwave plasma and a high-frequency plasma excited by said high-frequency power so as to be reactive species, and a deposit deposited inside said processing container is etched by said reactive species so as to be removed.
- 11. (Original) The method according to claim 10, wherein said deposit contains a fluorine-added carbon film.